

Features

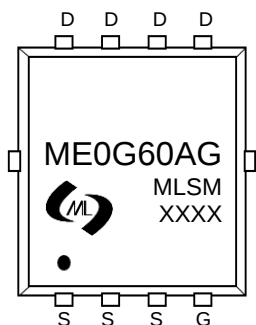
- Split gate trench MOSFET technology
- High density cell design for ultra low RDS(ON)
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation

Application

- Power switching application
- Load Switch

Product Summary

V _{DS}	R _{DS(ON)} TYP	I _D
60V	5.0mΩ@10V	60A
	6.7mΩ@4.5V	



Marking and pin assignment

ME0G60AG: Device code
XXXX : Code



PDFN3X3-8L view



Schematic diagram



Halogen-Free

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

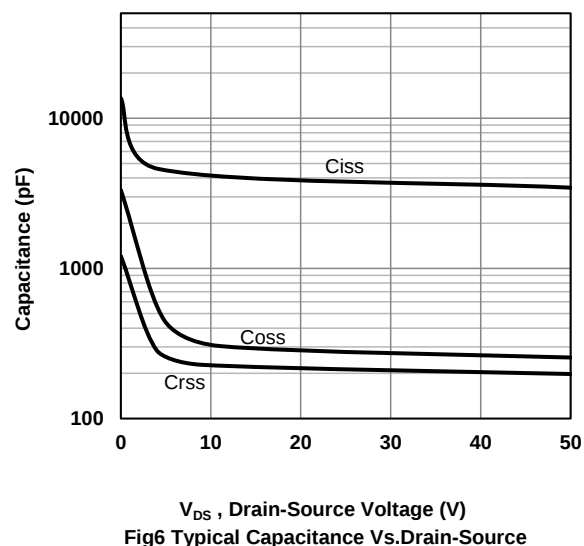
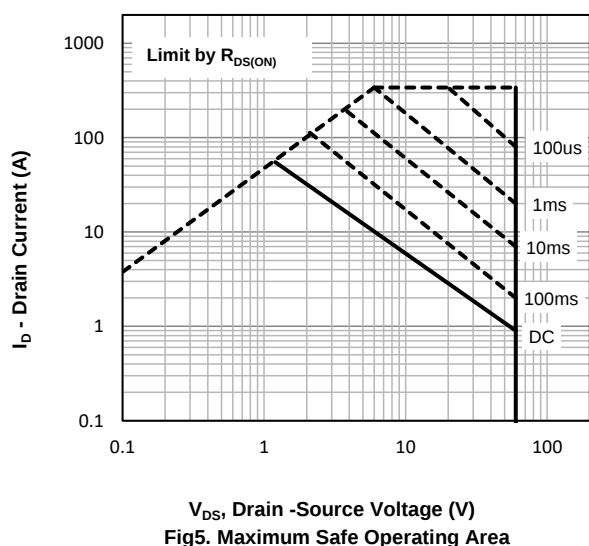
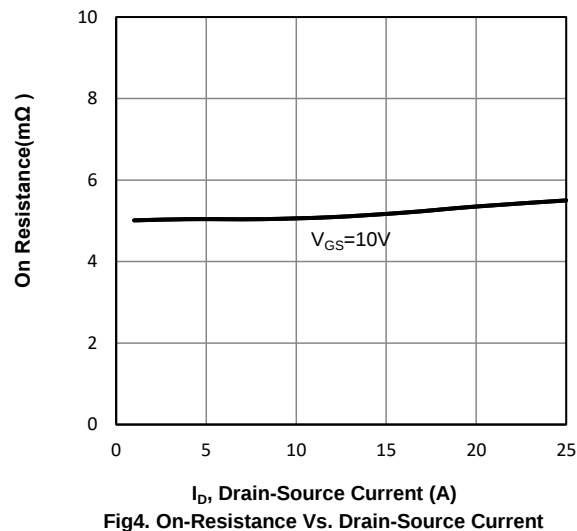
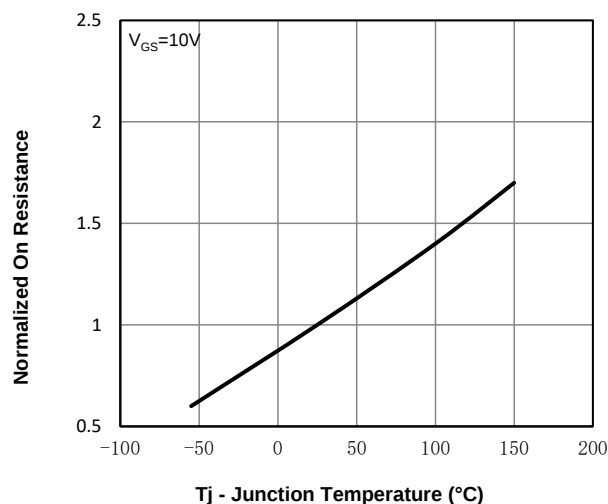
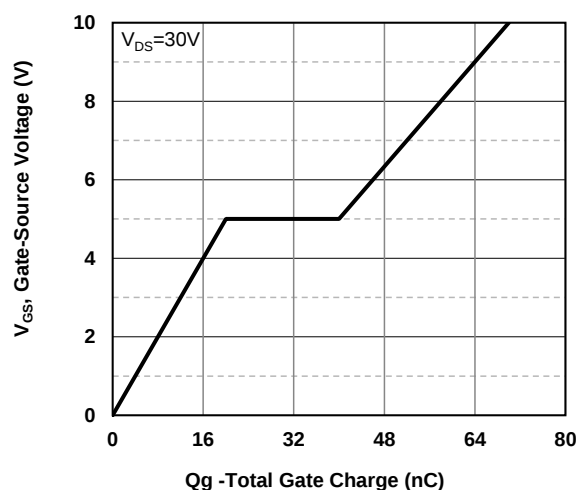
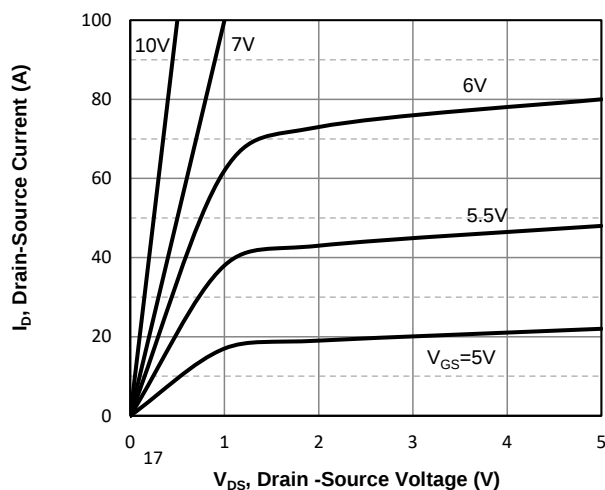
Symbol	Parameter		Rating	Unit
Common Ratings (TC=25°C Unless Otherwise Noted)				
V _{DS}	Drain-Source Breakdown Voltage		60	V
V _{GS}	Gate-Source Voltage		±20	V
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-50 to 155	°C
I _S	Diode Continuous Forward Current	Tc=25°C	60	A
Mounted on Large Heat Sink				
I _{DM}	Pulse Drain Current Tested	Tc=25°C	300	A
I _D	Continuous Drain Current	Tc=25°C	60	A
P _D	Maximum Power Dissipation	Tc=25°C	50	W
R _{θJA}	Thermal Resistance Junction-to-Ambient		40	°C/W

Ordering Information (Example)

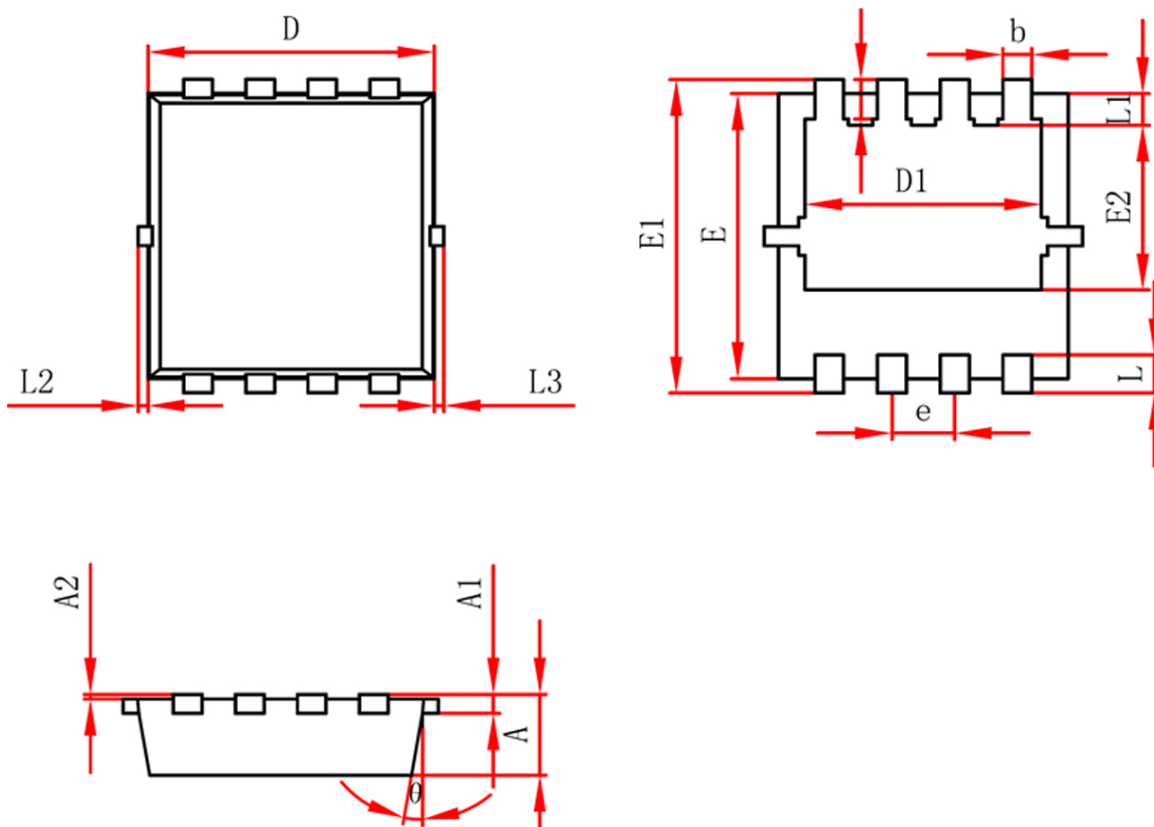
Type	Package	Marking	Minimum Package(pcs)	Inner Box Quantity(pcs)	Outer Carton Quantity(pcs)	Delivery Mode
ME0G60AG	PDFN3X3-8L	ME0G60AG	5,000	10,000	70,000	13"reel

Electrical Characteristics (TJ=25°C unless otherwise noted)						
Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
BV _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	60	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =60V, V _{GS} =0V	--	--	1.0	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V	--	--	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.0	--	2.5	V
R _{DS(on)}	Drain-Source On-State Resistance	V _{GS} =10V, I _D =20A	--	5.0	5.7	mΩ
		V _{GS} =4.5V, I _D =15A	--	6.7	8.0	mΩ
Dynamic Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
C _{ISS}	Input Capacitance	V _{DS} =25V, V _{GS} =0V, f=1MHz	--	3782	--	pF
C _{OSS}	Output Capacitance		--	297	--	pF
C _{RSS}	Reverse Transfer Capacitance		--	218	--	pF
Switching Characteristics						
Q _g	Total Gate Charge	V _{DS} =30V, I _D =20A, V _{GS} =10V	--	77	--	nC
Q _{gs}	Gate Source Charge		--	21	--	nC
Q _{gd}	Gate Drain Charge		--	24	--	nC
t _{d(on)}	Turn-on Delay Time	V _{DS} =30V, I _D =20A, V _{GS} =10V, R _G =1.8Ω	--	18	--	nS
t _r	Turn-on Rise Time		--	88	--	nS
t _{d(off)}	Turn-Off Delay Time		--	37	--	nS
t _f	Turn-Off Fall Time		--	85	--	nS
Source- Drain Diode Characteristics						
V _{SD}	Forward on voltage	Tj=25°C, Is=10A	--	--	1.2	V

Typical Operating Characteristics



PDFN3X3-8L Package information



Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	0.750	0.850	0.030	0.034
A1	0.152 REF.		0.006 REF.	
A2	0~0.05		0~0.002	
D	2.950	3.150	0.117	0.125
D1	2.400	2.500	0.095	0.099
E	2.950	3.050	0.117	0.121
E1	3.250	3.350	0.129	0.132
E2	1.685	1.785	0.067	0.071
b	0.250	0.350	0.010	0.014
e	0.600	0.700	0.024	0.028
L	0.350	0.450	0.014	0.018
L1	0.325	0.425	0.013	0.017
L2	0~0.100		0~0.004	
L3	0~0.100		0~0.004	
H	0.365	0.465	0.014	0.018
θ	10°	12°	10°	12°